

## IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A semiconductor device ~~characterized in that~~ comprising:

a gate interconnection and a source interconnection ~~[[are]]~~ formed ~~[[on]]~~ over a substrate ~~are formed on the same plane~~; and  
~~the gate interconnection and the source interconnection intersect through~~ an insulating film formed between the gate interconnection and the source interconnection in a region where the gate interconnection and the source interconnection intersect.

2. (Currently amended) A semiconductor device ~~characterized in that~~ comprising:

a gate interconnection and a source interconnection ~~[[are]]~~ formed ~~[[on]]~~ over a substrate ~~are formed on the same plane~~, and  
~~the gate interconnection and the source interconnection intersect through~~ an island-like insulating film formed between the gate interconnection and the source interconnection in a region where the gate interconnection and the source interconnection intersect.

3. (Currently amended) A semiconductor device comprising ~~a source interconnection and a gate interconnection over a substrate, the semiconductor device characterized in that~~:

a gate interconnection and a source interconnection formed over a substrate; and

an island-like insulating film ~~[[is]]~~ formed between the gate interconnection and the source interconnection in a region where the gate interconnection and the source interconnection intersect;

[[and]]

wherein the gate interconnection and the source interconnection are formed on a same insulating surface in a region where the gate interconnection and the source interconnection do not intersect.

4. (Currently amended) A semiconductor device according to ~~claim 2 or 3~~ characterized in ~~that:~~ any one of claims 2 and 3,

wherein the island-like insulating layer is formed so as to cover the gate interconnection in a region where the gate interconnection and the source interconnection intersect; and

wherein the source interconnection is formed over the island-like insulating layer.

5. (Currently amended) A semiconductor device according to ~~claim 2 or 3~~ characterized in ~~that:~~ any one of claims 2 and 3,

wherein the island-like insulating layer is formed so as to cover the source interconnection in a region where the gate interconnection and the source interconnection intersect; and

wherein the gate interconnection is formed over the island-like insulating layer.

6. (Currently amended) A semiconductor device comprising ~~a source region and a source interconnection over a substrate, the semiconductor device characterized in that:~~

a source region and a source interconnection formed over a substrate; and

the source region and the source interconnection [[are]] connected on a same plane.

7. (Currently amended) A semiconductor device according to claim 5 ~~characterized in that:~~

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wherein the source region and the source interconnection are connected without through a contact hole.

8. (Currently amended) A semiconductor device according to any one of claims 1 to 3 ~~characterized in that:~~

wherein at least one of the gate interconnection and the source interconnection is formed by discharging a solution containing metal particles.

9. (Currently amended) A semiconductor device according to any one of claims 1 to 3 ~~characterized in that:~~

wherein at least one of the gate interconnection and the source interconnection is formed by discharging a solution containing metal elements.

10. (Currently amended) A semiconductor device according to claim 1 ~~characterized in that:~~

wherein the insulating film is formed by discharging a solution containing an insulating material.

11. (Currently amended) A semiconductor device according to any one of claims 2 and 3 ~~characterized in that:~~

wherein the island-like insulating layer is formed by discharging a solution containing an

insulating material.

12. (Currently amended) A semiconductor device according to any one of claims 1 to 3 and  
5 ~~characterized in that:~~

wherein the semiconductor device includes a thin film transistor using a microcrystalline  
semiconductor.

13. (Currently amended) A semiconductor device according to any one of claims 1 to 3 and  
5 ~~characterized in that:~~

wherein the semiconductor device includes a thin film transistor using an organic  
semiconductor.

14. (Currently amended) A method for manufacturing a semiconductor device ~~characterized~~  
~~in that the semiconductor device is formed by~~ comprising the steps of:

forming a gate interconnection over a substrate;

forming an island-like insulating layer so as to selectively cover the gate interconnection; and

forming a source interconnection on a same plane of the gate interconnection,

~~wherein the gate interconnection and the source interconnection are formed so as to intersect~~  
~~through~~ the insulating layer is formed between the gate interconnection and the source  
interconnection in a region where the gate interconnection and the source interconnection intersect.

15. (Currently amended) A method for manufacturing a semiconductor device ~~characterized~~

~~in that the semiconductor device is formed by~~ comprising the steps of:

forming a source interconnection over a substrate;

forming an island-like insulating layer so as to selectively cover the source interconnection;

and

forming a gate interconnection on a same plane of the source interconnection,

~~wherein the source interconnection and the gate interconnection are formed so as to intersect~~  
~~through the insulating layer~~ is formed between the source interconnection and the gate interconnection in a region where the source interconnection and the gate interconnection intersect.

16. (Currently amended) A method for manufacturing a semiconductor device ~~characterized~~  
~~in that the semiconductor device is formed by~~ comprising the steps of:

forming a gate interconnection over a substrate;

forming an island-like insulating layer so as to selectively cover the gate interconnection; and

forming a source interconnection on a same plane of the gate interconnection or the island-like insulating layer.

17. (Currently amended) A method for manufacturing a semiconductor device according to any one of claims 14 to 16 ~~characterized in that:~~

wherein at least one of the gate interconnection or the source interconnection is formed by discharging a solution containing metal particles.

18. (Currently amended) A method for manufacturing a semiconductor device according to

any one of claims 14 to 16 ~~characterized in that:~~

wherein at least one of the gate interconnection or the source interconnection is formed by discharging a solution containing metal elements.

19. (Currently amended) A method for manufacturing a semiconductor device according to any one of claims 14 to 16 ~~characterized in that:~~

wherein the island-like insulating layer is formed by discharging a solution containing a insulating material.

20. (Currently amended) A method for manufacturing a semiconductor device according to any one of claims 14 to 16 ~~characterized in that:~~

wherein the gate interconnection and the source interconnection are formed by using a laser drawing device.

21. (Original) A display device including the semiconductor device according to any one of claims 1 to 3 and 5.

22. (Original) A digital still camera including the semiconductor device according to any one of claims 1 to 3 and 5.

23. (Original) A personal computer including the semiconductor device according to any one of claims 1 to 3 and 5.

24. (Original) A mobile computer including the semiconductor device according to any one of claims 1 to 3 and 5.

25. (Original) An image reproducing system including the semiconductor device according to any one of claims 1 to 3 and 5.